

Monolithic Amplifier

TSS-13HLN+

Mini-Circuits

50Ω 1 MHz to 1 GHz

THE BIG DEAL

- Ultra-High IP3, +42.9 dBm typ.
- Gain, 23 dB typ. at 0.5 GHz
- Medium power, +28.4 dBm typ.
- Excellent Noise Figure, 1.4 dB typ.
- Shutdown feature
- Suitable for low phase noise applications



Generic photo used for illustration purposes only CASE STYLE: DQ1225

+RoHS Compliant The +Suffix identifies RoHS Compliance. See our website for methodologies and qualifications

APPLICATIONS

- Base station infrastructure
- CATV
- Cellular

PRODUCT OVERVIEW

TSS-13HLN+ (RoHS compliant) is an advanced wideband amplifier with shutdown feature. It is fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the TSS-13HLN+ has good input and output return loss over a broad frequency range. TSS-13HLN+ is enclosed in a 3x3mm, 12-lead MCLP package and has very good thermal performance.

KEY FEATURES

Feature	Advantages			
Broad Band: 1 MHz to 1 GHz	Broadband covering primary wireless communications bands: VHF, UHF, Cellular			
Extremely High IP3 +40.6 dBm typical at 1 MHz +42.9 dBm typical at 0.5 GHz	The TSS-13HLN+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being approximately 14-15 dB above the P1dB point. This feature makes this amplifier ideal for use in: • Driver amplifiers for complex waveform up converter paths • Drivers in linearized transmit systems • Secondary amplifiers in ultra-High Dynamic range receivers			
Shutdown feature	Allow users to turn on and off the amplifier with pulsed signals while keeping the power supply at constant voltage to minimize DC power consumption			
Low Noise Figure 1.4 dB at 0.5 GHz	Enables lower system noise figure performance and along with High OIP3 provides high dynamic range			
High P1dB, +28.4 dBm at 0.5 GHz	High P1dB, High OIP3, Low NF results in a very dynamic range preventing amplifier saturation under strong interfering signals.			
Low additive phase noise, typically -162 dBc/ Hz @10 KHz offset	Ideal for low phase noise synthesizer applications			





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ELECTRICAL SPECIFICATIONS¹ AT +25°C & 50Ω, UNLESS NOTED OTHERWISE

Parameter	Condition (MHz)	Vd = +8V		Vd = +5V		Vd = +3V		
		ON State	OFF State	ON State	OFF State	ON State	OFF State	Units
Frequency Range		1-1000	1-1000	1-1000	1-1000	1-1000	1-1000	MHz
	1	3	_	3.1	_	3	_	
	20	1.4	_	1.1	_	1.1	_	
Noise Figure	250	1.3	_	1.1	_	1.1	_	dB
	500	1.4	_	1.1	_	1.1	_	uD
	1000	1.6	_	1.2	_	1.3	_	
Additive Phase Noise 1.0 GHz, 10KHz offset		-162				2.0		dBc/Hz
····· · · · · · · · · · · · · · · · ·	1	25	-24	24.7	-24	23.9	-24	
	20	24.4	-22	24.2	-21	23.5	-22	
Gain	250	23.2	-21	23	-21	22.3	-21	dB
duin	500	23	-22	22.8	-22	21.9	-22	GD
	1000	21.1	-26	20.9	-27	19.5	-27	
Reversed Isolation	1-1000	26	27	20.5	27	26	27	dB
	1-1000	11	12	11	12	10	12	UD UD
	20	16	12	15	12	10	12	
law at Data wall and		10	12		12	15	12	-10
Input Return Loss	250			18				dB
	500	20	12	21	12	17	12	
	1000	14	10	14	10	10	10	
	1	11	1	11	1	11	1	dB
- · · - · ·	20	19	2	19	2	21	2	
Output Return Loss	250	18	2	18	2	21	2	
	500	33	2	25	2	21	2	
	1000	12	2	11	2	10	2	
	1	25.2		+20.3		+14.2		
	20	26.7		+22.4		+16.3		
Output Power @1dB compression AMP-ON	250	28		+24.1		+19.3		dBm
	500	28.4		+24.5		+19.5		
	1000	26.7		+23.4		+18.3		
	1	40.6		+38.4		+31.6		
Quart ID2	20	41.3		+40.3		+33.2		
Ouput IP3 (Pout = 0dBm/Tone)	250	41.2		+39.6		+34.4		dBm
(Pout – Vabrii/ Tone)	500	42.9		+39.2		+33		
	1000	40.8		+36.2		+29.4		
Device Operating Voltage(VDD)		+8	+8	+5	+5	+3	+3	V
Device Operating Current(ID) ⁴		234	7.5	142	5	72	3	mA
Control Voltage (VG)		0	+5	0	+5	0	+5	V
Device Current Variation vs. Temperature ³		-136		10		33		uA/degC
Device Current Variation vs. Voltage		0.025		0.025		0.033		mA/mV
Thermal Resistance		23.3		23.3		23.3		degC/W

1. Measured on Mini-Circuits Characterization test board TB-TSS-13HLN+. See Characterization Test Circuit (Fig. 1)

2. (Current at 95°C – Current at -45°C)/140

ABSOLUTE MAXIMUM RATINGS³

Parameter	Ratings		
Operating Temperature (ground lead)	-40°C to +95°C		
Storage Temperature	-65°C to +150°C		
Total Power Dissipation	3.3W		
Input Power	+28 dBm (5 minutes max.) +10 dBm (continuos) for 1- 30 MHz +18 dBm (continuos) for 0.03-1 GHz		
DC Voltage V_{DD}^4 (Pad 7)	+10 V		
DC Voltage V _G ⁵ (Pad 1)	+10 V		

3 Permanent damage may occur if these limits are exceeded.

4 Measured by keeping VG=0V. 5 Measured by keeping Vdd=8V.

CONTROL VOLTAGE (V_c) FIG. 1

	Min.	Тур.	Max.	Units
Amplifier-ON	_	0	0.7	V
Amplifier-OFF	1.9	5	—	V



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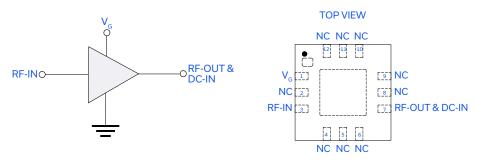
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SWITCHING SPECIFICATIONS

Parameter		Min.	Тур.	Max.	Units	
Amerilifian Oblita Chutalaum	OFF TIME (50% Control to 10% RF)	_	5.3	_	μs	
Amplifier ON to Shutdown	FALL TIME (90 to 10% RF)	_	7.3	_		
Amplifier Shutdown to ON	ON TIME (50% Control to 90% RF)	_	77.7	_	μs	
	RISE TIME (10% to 90% RF)	_	54.2	_		
Control Voltage Leakage		—	633.3	—	mV	

SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION



Function	Pad Number	Description
RF-IN	3	RF Input
RF-OUT and DC-IN	7	RF Output and DC Bias
GND	Paddle	Connections to ground.
NC	2, 4-6, 8-12	No connection, grounded externally
VG	1	Control voltage for shutdown (VG)



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CHARACTERIZATION TEST CIRCUIT / RECOMMENDED APPLICATION CIRCUIT

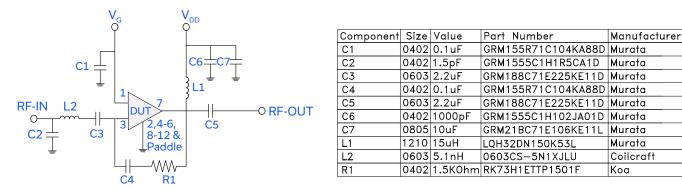


Fig 1. Block diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-TSS-13LN+) Gain, Return loss, Output power at 1dB compression (P1dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

- 1. Gain and Return Loss: P_{IN}= -25dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, +0dBm/tone at output.
- 3. Switching Time
- RF Signal: P_{IN} =-25 dBm, fRF=500 MHz. Vdd=8V DC, VG=Pulse signal at 1 KHz with VHIGH=5V, VLOW=0V, 50% duty cycle.

PRODUCT MARKING



Marking may contain other features or characters for internal lot control



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ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASHBOARD. CLICK HERE

Performance Data	Data Table Swept Graphs S-Parameter (S2P Files) Data Set (.zip file)	
Case Style	DQ1225 Plastic package, exposed paddle lead finish: Matte-Tin	
Tape & Reel Standard quantities available on reel	F66 7" reels with 20, 50, 100, 200, 500, 1K, or 2K devices	
Suggested Layout for PCB Design	PL-623	
Evaluation Board	TB-TSS-13HLN+	
Environmental Ratings	ENV08T9	

ESD RATING

Human Body Model (HBM): Class 1A (Pass 250 V) in accordance with ANSI/ESD STM 5.1 - 2001

NOTES

A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.

B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.

C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/terms/viewterm.html



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